

# NEC's 3 V DUAL DOWNCONVERTER AND PLL FREQUENCY SYNTHESIZER

## **UPB1007K**

#### **FEATURES**

INTEGRATED RF BLOCK:
 LNA, RF & IF Downconverter + PLL frequency synthesizer

• STATE OF THE ART 25 GHz ft UHS0 BIPOLAR PROCESS

DOUBLE-CONVERSION: f1stIF = 61.380 MHz
 f2ndIF = 4.092 MHz

• ADJUSTABLE GAIN: 20 dB range MIN

• FIXED DIVISION PRESCALER

LOW POWER CONSUMPTION: 25 mA @ 3 V

SMALL 36 PIN QFN PACKAGE
 Flat lead style for better performance

TAPE AND REEL PACKAGING AVAILABLE

#### DESCRIPTION

NEC's UPB1007K is a Silicon RFIC designed for low cost GPS receivers. The IC combines an LNA, followed by a double-conversion RF/IF downconverter block and a PLL frequency synthesizer on one chip. The device operates on a 3V supply voltage and is housed in a small 36 pin QFN (Quad Flat Nolead) package, resulting in low power consumption and reduced board space. The device is manufactured using the state of the art UHS0 25 GHz fT silicon bipolar process. NEC's stringent quality assurance and test procedures ensure the highest reliability and performance.

#### **APPLICATIONS**

- LOW POWER HANDHELD GPS RECEIVER
- IN-VEHICLE NAVIGATION SYSTEMS
- PC/PDA+GPS INTEGRATION

### **ELECTRICAL CHARACTERISTICS** (TA = 25°C, Vcc = 3.0 V, unless otherwise specified)

	PART NUMBER PACKAGE OUTLINE			UPB1007K QFN-36	
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
Icc	Total Circuit Current, No Signals	mA		25	31
Vcc	Supply Voltage	V	2.7	3.0	3.3
LNA (fRFin	= 1575.42 MHz, ZL = Zs = 50 Ω)				
ZLNAin	RF Input Impedance of LNA	Ω		28 - j38	
ZLNAop	RF Output Impedance of LNA	Ω		85 - jx6	
P1dBLNA	1 dB Compression, Input matched	dBm		-22	
PGLNA	Power Gain LNA, Input matched, PRFin = -60 dBm	dB	14	15	
NFLNA	Noise Figure of LNA, Input matched	dB		2.8	3.2
Mixer (fRFin = 1575.42 MHz, f1stL0in = 1636.80 MHz, PLo = -10 dBm, f1stlF = 61.38 MHz, ZL = Zs = 50 Ω)					
ZMIXin	RF Input Impedance of Mixer	Ω		31 -j103	
P <sub>1dBMIX</sub>	1 dB Compression (refer to input), Input matched	dBm		-25	
РССміх	Power Conversion Gain	dB		21	
NFMIX	Noise Figure of Mixer (SSB), Input matched	dB		9.5	10
ALO-IF	LO Leakage to IF Pins, PLO = -10 dBm	dBm		-40	
ALO-RF	LO Leakage to RF Input Pins, PLo = -10 dBm	dBm		-48	
ZMIXout	RF Output Impedance of Mixer			+152 - j9	
PLL					
Ісрон	PLL Charge Pump High Side Current @ VcPout = Vcc/2	mA		1	
ICPOL	PLL Charge Pump Low Side Current @ VcPout = Vcc/2	mA		-1	
fpD	Phase Comparison Frequency	MHz		8.184	
IF Down	converter Block (f1stlFin = 61.38 MHz, f2ndLOin = 65.472 I	MHz, f2ndIF O	utput = 4.092 MHz,	$Zs = 2k\Omega$ , $ZL = 2 k\Omega$ )	
NF2ndMIX	Noise Figure of 2nd IF Mixer (SSB), (Zs = $50\Omega$ )	dB		12	
GV2ndMIX	Voltage Gain of 2nd Mixer/Amplifier, P1stlF = -50 dBm	dB		47	
Vgc	Gain Control Voltage (Voltage at maximum gain)	V		0.5	
Dgc	Gain Control Range, P1stlF = -50 dBm (Voltage at maximum gain)	dB	20		
A2ndLO1stIF	2nd LO Isolation to 1st IF Input Pins, VAGC = 0 V	dB		-70	
A2ndLO2ndIF	2nd LO Isolation to 2nd IF Output Pins, VAGC = 0 V	dB		-70	

California Eastern Laboratories

## **ELECTRICAL CHARACTERISTICS** (TA = 25°C, Vcc = 3 V, unless otherwise specified)

	PART NUMBER PACKAGE OUTLINE	_		UPB1007K QFN-36	
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
2nd IF Am	plifier Block (f2ndIF = 4.096 MHz, Zs = 2k $\Omega$ , ZL = 2 k $\Omega$ )				
GVым	Voltage Gain of Limiter Amplifier, PIN = -60 dBm	dB		48	
fвв	Roll-off Frequency	MHz		110	
Reference	Amplifier Block				
VREFin	Reference Input Minimum Level	mVpp	400	400	
VREFout	Reference Output Swing (open collector output), $CL = 2 \text{ pF//RL} = 10 \text{ k}\Omega$	Vpp	1.1	1.2	1.3
Power Dov	wn Control Pins				
VIH	Digital Control Input High	V	1.83	1.86	2.15
VIL	Digital Control Input Low	V		0.5	0.6

## **ABSOLUTE MAXIMUM RATINGS<sup>1,2</sup>** (TA = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
Vcc	Supply Voltage	V	3.6
Рт	Total Power Dissipation <sup>3</sup>	mW	433
Тор	Operating Temperature	°C	-40 to +85
Тѕтс	Storage Temperature	°C	-55 to +150

#### Notes:

- 1. Operation in excess of any one of these parameters may result in permanent damage.
- 2. More than two items must not be reached simultaneously.
- 3. TA = +85°C, mounted on a 50 x 50 x 1.6 mm double-sided copper clad epoxy glass PWB.

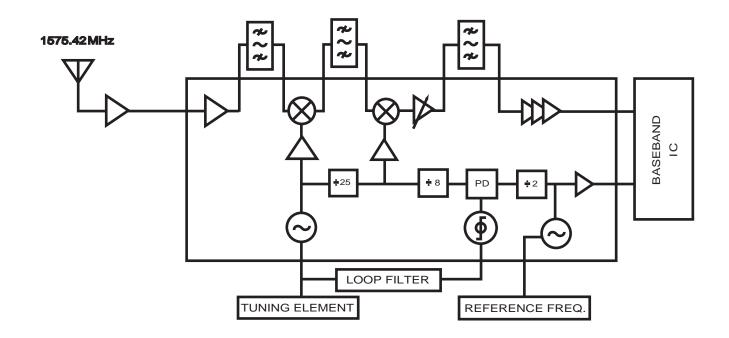
# RECOMMENDED OPERATING CONDITIONS

SYMBOLS	PARAMETERS	UNITS	MIN	TYP	MAX
Vcc	Supply Voltage	V	2.7	3.0	3.3
Тор	Operating Temperature	°C	-40	+25	+85
fRFin	RF Input Frequency	MHz		1575.42	
fREFin fREFout	Reference Frequency	MHz		16.368	
f1stL0	1st LO Oscillating Frequency	MHz		1636.8	
f1stlFin	1st IF Input Frequency	MHz		61.38	
f2ndLOin	2nd LO Input Frequency	MHz		65.472	
f2ndIFin f2ndIFout	2nd IF Input/Output Frequency	MHz		4.092	
VIH	Power Down Control Voltage "High"	<b>\</b>	1.8		3
VIL	Power Down Control Voltage "Low"	V			0.6

## **CURRENT BUDGET**

SYMBOL	PARAMETER AND CONDITIONS	UNITS	MIN	TYP	MAX
IC Performance Parameters					
Vcc	Supply Voltage	V	2.7	3.0	3.3
Icc	Total Circuit Current, Vcc = 3.0 V, no signal	mA		25	31
ICC_PL	Power Down Node Current	mA		0.15	
lcc_xo	Oscillator Supply Current, (Pin 15 = 0 V, Pin 16 = 3 V)	mA		2.7	
ICC_RX	Receiver Supply Current, (Pin 15 = 0 V, Pin 16 = 3 V)	mA		22.3	
Functiona	al Blocks Current Details		1	1	
ICC_LNA	Supply Current of LNA, RF off	mA		2.6	
ICC_MIX1	Supply Current of RF Mixer, RF off	mA		6.7	
ICC_MIX2	Supply Current of IF Mixer, RF off	mA		3.5	
ICC_IFAMP	Supply Current of IF Amplifier, RF off	mA		1.1	
lcc_xo	Crystal Oscillator Supply Current	mA		2.7	
Icc9	PLL Supply Current	mA		6.3	
ICC_CF	Control Functions Supply Current	μΑ		2.1	
VIL	Power Down Pin Logic LOW Level	V			0.6
VIH	Power Down Pin Logic HIGH Level	V	1.8		
$ au_{ extsf{d}\_ extsf{PON}}$	Power-on Response Time	ms		3	

## APPLICATION EXAMPLE



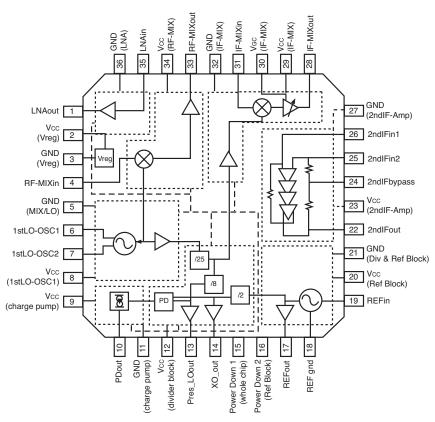
Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
1	LNAout	Output pin of LNA. Output biasing and matching required as it is an open collector output.	2 <b>1</b>
2	VCC (Vreg)	Supply voltage pin of regulator mixer block.	35
3	GND (Vreg)	Ground pin of regulator reference cell.	Regulator B A A A A A A A A A A A A A A A A A A
4	RF MIXin	Input pin of RF mixer. 1575.42 MHz band pass filter can be inserted between pin 1 and mixer input.	T=1.2K  T=1.2K  T=1.2K  T=1.2K  T=1.2K  T=1.2K  T=1.2K
5	GND (MIX)	Ground pin of RF mixer cell.	21 6
6	1stLO-OSC1	Pins 6 & 7 are base pins of the differential amplifier for 1st LO oscillator. These pins	
7	1stLO-OSC2	should be equipped with LC and varactor circuits to oscillate at 1636.8 MHz.	r=275 r=275
8	Vcc (1stLO-OSC)	Supply voltage pin of differential amplifier for 1st LO oscillator circuit (VCO).	Regulator  Sign idc=lbias  21
9	Vcc (Charge Pump)	Supply voltage pin of the phase detector charge pump.	9
10	PD-out	This is a current mode charge pump output for connection to a passive RC loop filter for driving the external varactor diode of 1stLO-OSC.	Source Control
11	GND (Charge Pump)	Ground pin of phase detector charge pump.	From PFD Sink Control

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
12	Vcc (Divider Block)	Supply voltage pin of prescaler, phase detector, crystal oscillator, VCO buffer.	12
13	LO_out	Monitor pin of frequency at phase detector.	From PFD Input  13,(14)
14	XO_out	Monitor pin of oscillator ÷2 output at phase detector.	ESD ESD
15	PD1	Power down control pin Low = Whole chip off except XTAL osc. High = Whole chip on except XTAL osc.	Vcc •
16	PD2	Reference block standby mode. Low = Reference block disabled. High = Reference block enabled.	15,(16) ESD  ESD  2
17	REFout	Output pin of reference frequency. The frequency from pin 17 can be taken out as 1Vp-p swing.	From XO  ESD  17  From XO  21

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
18	REF gnd	Differential oscillator input. This pin should be grounded via a capacitor.	12
19	REFin	Input pin of the reference frequency buffer. This pin should be equipped with an external 16.368 MHz oscillator (e.g. TCXO).	ESD = 1.5K
20	Vcc (Ref Block)	Supply voltage pin of output charge pump of the oscillator.	idc = 30u  idc = 1m
21	GND (Ref Block)	Ground pin of the oscillator, prescaler, phase detector and VCO.	21
22	2nd IFout	Output pin of 2nd IF amplifier. This pin output 4.092 MHz clipped sinewave. This pin should be equipped with external inverter to adjust level to next stage on user's system.	23 <b></b>
23	Vcc 2ndIFAMP	Supply voltage pin of 2ndIF amplifier	26 P Q
24	2ndIF bypass	Bypass pin of 2nd IF amplifier input. This pin should be grounded via a capacitor.	25 ×
25	2ndlFin1	Pin 1 of 2nd IF amplifier input . 2nd IF filter can be inserted between 25 & 28.	TSD TSD TSD
26	2ndlFin2	Pin 2 of 2nd IF amplifier input. This pin should be grounded via a capacitor.	27 🌑
27	GND (2ndIF AMP)	Ground pin of 2nd IF amplifier.	
28	IF MIXout	Output pin from IF mixer. IF mixer output signal goes through gain control amplifier before this emitter follower output port.	From IF Mix / AGC  ESD  28
29	Vcc (IF MIX)	Supply voltage pin of IF mixer, gain control amplifier.	idc=400u ESD

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
30	Vgc (IF MIX)	Gain control voltage pin of IF mixer output amplifier. This voltage performs forward control, i.e., (Vgc up→Gain down).	29
31	IF-MIXin	Input pin of IF mixer and IF VAGC.	29 F=1.2K
32	GND (IF-MIX)	Ground pin of IF mixer and IF VAGC.	31 ESD idc=32u idc=100u
33	RF-MIXout	Output pin of RF mixer . 1st IF filter must be inserted between pins 31 and 33.	From RF Mixer ESD
34	Vcc (RF-MIX)	Supply voltage pin of RF mixer block. This pin must be decoupled with capacitor (e.g. 1000 pF).	idc=1.1m ESD
35	LNAin	Input pin of low noise amplifier. Optimal input matching required for low noise performance.	See Pins 1-3
36	GND (LNA)	Ground pin of LNA.	

### INTERNAL BLOCK DIAGRAM



#### ORDERING INFORMATION

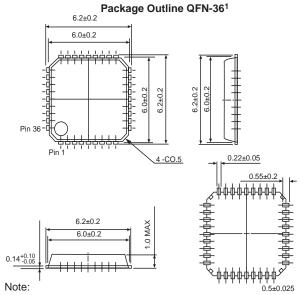
Part Number	Package
UPB1007K	36 Pin plastic QFN

### ACTUAL SIZE (Units in mm)

#### Package Outline QFN-36



## **OUTLINE DIMENSIONS** (Units in mm)



1. The solder pads on each corner should be grounded.

#### Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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